ARCADIA at Fermilab

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Updates:

Fe55 measurement – X-ray fluorescence





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1) To better understand frontside-backside discrepancies in terms of shift of the S-curve:

- Measurements with higher statistics and control over temperature with ⁵⁵Fe source;
- Improved MC simulation: randomly generated electrons cloud width, possibility to simulate a N x N pixel matrix, etc ... ;

2) To calibrate the sensor threshold range, more energies are required:

• Measurements with monochromatic source at a different energies \rightarrow X-rays fluorescence

X-ray s-curve fit model: recap





$$N(t) = N_0 \left(1 + \frac{C_S}{\sigma} (t_0 - t) \right) \left(1 + erf\left(\frac{(t_0 - t)}{\sigma}\right) \right)$$

 C_S → Charge sharing contribution σ → Electronic noise



t : threshold t₀: threshold at which the s-curve inflection point is found





Measurements with ⁵⁵Fe source @ T = 29 °C



Front-Back pixel (345,275)

The shift is clearly still evident

Temperature was measured every 30 seconds with a probe placed on ARCADIA Front-End Board







How do we explain the S-curves shift?

Main hypothesis: charge sharing effects among neighbour pixels. In the backside configuration charges diffuse more because they are generated far from the collection electrodes.



Hint: even with a simulated MIP-like charge release (200 MeV μ^{-}), the average cluster size is of about 4 pixels.

Large charge sharing!

from C. Ferrero, C. Neubüser, L. Pancheri and A. Rivetti, "Monte Carlo simulations of Fully Depleted CMOS pixel sensors for radiation detection applications," *2023 18th Conference on Ph.D Research in Microelectronics and Electronics (PRIME)*, Valencia, Spain, 2023, pp. 101-104, doi: 10.1109/PRIME58259.2023.10161878.



Fig. 7. Average cluster size as function of the tilting angle for three different sensor thicknesses with a fixed threshold of 200 e^- . The double tilting technique is shown in solid line, while the y-tilting is displayed in dashed line.

Measurements varying the backside bias





Nominal working backside $V_{bias} = -90 V$

Idea: decreasing V_{bias} the electric field is modified, and the diffusion should be enhanced





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Single pixel Monte Carlo simulation to study geometrical charge sharing effects in both frontside and backside configuration

50000

40000

30000

20000

10000

Noise

0.0

0.2

Partial collection

1.0

ollected electrons/1640 electrons

Simulation is performed using the following steps:

- Generate hit coordinates (x, y) ٠
- Build a 2D gaussian with $\mu = (x, y)$ and ۲ fixed **w**
- Calculate numerical integral in pixel • area + electronic noise contribution
- Fill analog histogram \rightarrow S-curve •









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Single pixel Monte Carlo simulation to study geometrical charge sharing effects in both frontside and backside configuration

Simulation is performed using the following **steps**:

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Charge cloud width randomization:

- 1. Generate the X-ray interaction depth z: **Front**: $N(z) = N_0 \exp(-\mu z)$ **Back**: $N(z) = N_0 \exp(-\mu (200 - z))$ with 200 µm = ARCADIA thickness.
- From the interaction depth z, the charge cloud width w is computed assuming a simplified model:

$$w = \mathbf{\Delta} + \mathbf{k} \sqrt{z}$$

Simulation-data comparison

With this model, we can simulate both backside and frontside measurements tuning properly the the two parameters. We obtain a pair (Δ, \mathbf{k}) that reproduces well both s-curve shapes.



Backside data-simulation comparison for pixel (345,275)



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A good model should reproduce both backside and frontside measurements with the same calibrated xaxis (threshold calibration is only dependent on the pixel front-end).

However, this model is not able to reproduce the shift in t_0 we see in data.





Charge cloud: Model 2.0





Correction added to take into account the hit distance from the pixel center

 $w = \mathbf{\Delta} + \mathbf{k} \sqrt{z \cdot (1 + \mathbf{c} \cdot d(x, y))}$







Modified model works better, but there are three parameters to be tuned to reproduce data.

Model:
$$w = \Delta + k \sqrt{z \cdot (1 + c \cdot d(x, y))}$$

shape \checkmark
 t_0 position \checkmark
parameters \times

Next: AllPix2 to better simulate charge transport inside sensor





X-ray fluorescence measurements

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XR-100CR spectrum at 4mA Tests at different energies \rightarrow X-ray 5000 fluorescence setup with targets of 4000 different materials (Cu, Ti, Fe) From polychromatic X-ray tube 3000 spectrum to \sim monochromatic 2000 one impinging on ARCADIA X-ray tube (W) 1000 25 15 20 30 35 40 10 Energy [keV] Ti fluorescence spectrum 2000 1750 ARCADIA 1500 1250 1000 E_{XRF} (keV) Target Target (Ti) 750 Ti 4.51 500 250 Fe 6.40 8.05 Cu 2 10 Energy [keV]

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X-ray fluorescence S-curves

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X-ray fluorescence setup



Pros:

- gives the possibility to obtain
 ~ monochromatic photons at different energies, both higher and
 - lower than ⁵⁵Fe S-curves at different thresholds \rightarrow
- S-curves at different thresholds → possibility of calibration

Cons:

- Slow acquisition rate
- No control over temperature during the acquisitions
- Not feasible to use low energy X-rays (< 4.5 keV) because of their absorption in air